

# 4-Mbit (256 K × 16) Static RAM

#### **Features**

- Temperature ranges
  □ Industrial: –40 °C to 85 °C
- Pin and function compatible with CY7C1041BV33
- High speed
  □ t<sub>AA</sub> = 8 ns
- Low active power □ 360 mW (max)
- 2.0 V data retention
- Automatic power down when deselected
- TTL-compatible inputs and outputs
- Easy memory expansion with CE and OE features
- Available in Pb-free 44-pin TSOP II package

### **Functional Description**

The CY7C1041CV33 is a high performance CMOS static RAM organized as 262,144 words by 16 bits.

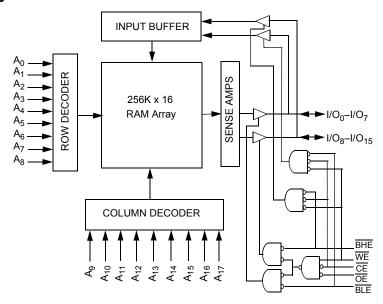
 $\overline{\text{To}}$  write to the device, take Chip Enable  $\overline{(CE)}$  and Write Enable  $\overline{(WE)}$  inputs LOW. If Byte Low Enable  $\overline{(BLE)}$  is LOW, then data from I/O pins (/IO<sub>0</sub> through I/O<sub>7</sub>), is written into the location specified on the address pins (A<sub>0</sub> through A<sub>17</sub>). If Byte High Enable (BHE) is LOW, then data from IO pins (I/O<sub>8</sub> through I/O<sub>15</sub>) is written into the location specified on the address pins (A<sub>0</sub> through A<sub>17</sub>).

To read from the device, take Chip Enable ( $\overline{\text{CE}}$ ) and Output Enable ( $\overline{\text{OE}}$ ) LOW while forcing the Write Enable (WE) HIGH. If Byte Low Enable (BLE) is LOW, then data from the memory location specified by the address pins appear on I/O<sub>0</sub> to I/O<sub>7</sub>. If Byte High Enable (BHE) is LOW, then data from memory appears on I/O<sub>8</sub> to I/O<sub>15</sub>. For more information, see the Truth Table on page 10 for a complete description of Read and Write modes.

The input and output pins (I/O $_0$  through I/O $_{15}$ ) are <u>placed</u> in a high impedance state when <u>the</u> device is des<u>elected</u> (<u>CE HIGH</u>), the outputs are <u>disabled</u> (<u>OE HIGH</u>), the <u>BHE</u> and <u>BLE</u> are <u>disabled</u> (<u>BHE</u>, <u>BLE HIGH</u>), or during a write operation (<u>CE LOW</u> and <u>WE LOW</u>).

For a complete list of related documentation, click here.

# **Logic Block Diagram**





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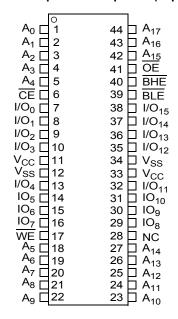


### **Selection Guide**

Description	-8	Unit
Maximum Access Time	8	ns
Maximum Operating Current	100	mA
Maximum CMOS Standby Current	10	mA

# **Pin Configurations**

Figure 1. 44-pin TSOP II pinout (Top View) [1]



#### Note

<sup>1.</sup> NC pins are not connected on the die.



# **Pin Definitions**

Pin Name	TSOP Pin Number	I/O Type	Description
A <sub>0</sub> -A <sub>17</sub>	1–5, 18–27, 42–44	Input	Address Inputs. Used to select one of the address locations.
I/O <sub>0</sub> –I/O <sub>15</sub>	7–10,13–16, 29–32, 35–38	Input or Output	<b>Bidirectional Data IO lines</b> . Used as input or output lines depending on operation.
NC	28	No Connect	No Connects. Not connected to the die.
WE	17	Input or Control	<b>Write Enable Input, Active LOW</b> . When selected LOW, a write is conducted. When deselected HIGH, a read is conducted.
CE	6	Input or Control	<b>Chip Enable Input, Active LOW</b> . When LOW, selects the chip. When HIGH, deselects the chip.
BHE, BLE	40, 39	Input or Control	Byte Write Select Inputs, Active LOW. $\overline{\rm BHE}$ controls I/O $_{15}$ –I/O $_{8},$ $\overline{\rm BLE}$ controls I/O $_{7}$ –I/O $_{0}.$
ŌĒ	41	Input or Control	Output Enable, Active LOW. Controls the direction of the I/O pins. When LOW, the IO pins are allowed to behave as outputs. When deasserted HIGH, the I/O pins are tri-stated and act as input data pins.
V <sub>SS</sub>	12, 34	Ground	Ground for the Device. Connected to ground of the system.
V <sub>CC</sub>	11, 33	Power Supply	Power Supply Inputs to the Device.



# **Maximum Ratings**

DC Input Voltage [2]	0.5 V to V <sub>CC</sub> + 0.5 V
Current into Outputs (LOW)	20 mA
Static Discharge Voltage (MIL-STD-883, Method 3015)	> 2001 V
Latch Up Current	> 200 mA

# **Operating Range**

Range	Ambient Temperature (T <sub>A</sub> )	V <sub>CC</sub>
Industrial	–40 °C to +85 °C	$3.3~\textrm{V}\pm10\%$

### **Electrical Characteristics**

Over the Operating Range

Dorometer	Description	Test Conditions		-8		
Parameter	Description	Test Conditions	Min	Max	Unit	
V <sub>OH</sub>	Output HIGH Voltage	$V_{CC}$ = Min, $I_{OH}$ = -4.0 mA	2.4	_	V	
$V_{OL}$	Output LOW Voltage	V <sub>CC</sub> = Min, I <sub>OL</sub> = 8.0 mA	-	0.4	V	
V <sub>IH</sub>	Input HIGH Voltage		2.0	V <sub>CC</sub> + 0.3	V	
V <sub>IL</sub> [2]	Input LOW Voltage		-0.3	0.8	V	
I <sub>IX</sub>	Input Leakage Current	$GND \le V_I \le V_{CC}$	-1	+1	μА	
I <sub>OZ</sub>	Output Leakage Current	$GND \le V_{OUT} \le V_{CC}$ , Output disabled	-1	+1	μА	
I <sub>CC</sub>	V <sub>CC</sub> Operating Supply Current	$V_{CC} = Max, f = f_{MAX} = 1/t_{RC}$	_	100	mA	
I <sub>SB1</sub>	Automatic CE Power Down Current – TTL Inputs	$\begin{aligned} &\text{Max V}_{\text{CC}}, \overline{\text{CE}} \geq \text{V}_{\text{IH}}, \\ &\text{V}_{\text{IN}} \geq \text{V}_{\text{IH}} \text{ or V}_{\text{IN}} \leq \text{V}_{\text{IL}}, \text{f = f}_{\text{MAX}} \end{aligned}$	_	40	mA	
I <sub>SB2</sub>	Automatic CE Power Down Current – CMOS Inputs	Max $V_{CC}$ , $\overline{CE} \ge V_{CC} - 0.3 \text{ V}$ , $V_{IN} \ge V_{CC} - 0.3 \text{ V}$ , or $V_{IN} \le 0.3 \text{ V}$ , f = 0	_	10	mA	

#### Note

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<sup>2.</sup>  $V_{IL}$  (min) = -2.0 V and  $V_{IH}$ (max) =  $V_{CC}$  + 0.5 V for pulse durations of less than 20 ns.



# Capacitance

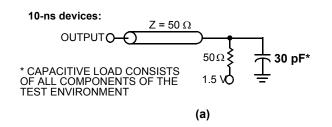
Parameter [3]	Description	Test Conditions	Max	Unit
C <sub>IN</sub>	Input Capacitance	$T_A = 25 ^{\circ}\text{C}, f = 1 \text{MHz}, V_{CC} = 3.3 \text{V}$	8	pF
C <sub>OUT</sub>	Output Capacitance		8	pF

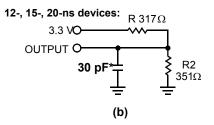
# **Thermal Resistance**

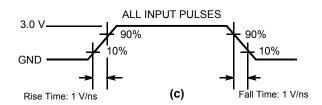
Parameter [3]	Description	Test Conditions	TSOP II	Unit
$\Theta_{JA}$	(Junction to Ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedance, per	42.96	°C/W
$\Theta_{JC}$	Thermal Resistance (Junction to Case)	EIA/JESD51	10.75	°C/W

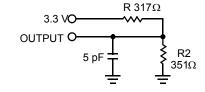
#### **AC Test Loads and Waveforms**

Figure 2. AC Test Loads and Waveforms [4]









(d)

High Z characteristics:

### Notes

- 3. Tested initially and after any design or process changes that may affect these parameters.
- A AC characteristics (except High Z) for 10-ns parts are tested using the load conditions shown in Figure 2 (a). All other speeds are tested using the Thevenin load shown in Figure 2 (b). High Z characteristics are tested for all speeds using the test load shown in Figure 2 (d).



# **Switching Characteristics**

Over the Operating Range

D (5)			-8		
Parameter [5]	Description	Min	Max	Unit	
Read Cycle			•		
t <sub>power</sub> <sup>[6]</sup>	V <sub>CC</sub> (Typical) to the First Access	100	_	μS	
t <sub>RC</sub>	Read Cycle Time	8	-	ns	
t <sub>AA</sub>	Address to Data Valid	_	8	ns	
t <sub>OHA</sub>	Data Hold from Address Change	3	-	ns	
t <sub>ACE</sub>	CE LOW to Data Valid	_	8	ns	
t <sub>DOE</sub>	OE LOW to Data Valid	_	5	ns	
t <sub>LZOE</sub>	OE LOW to Low Z <sup>[7]</sup>	0	-	ns	
t <sub>HZOE</sub>	OE HIGH to High Z <sup>[7, 8]</sup>	_	4	ns	
t <sub>LZCE</sub>	CE LOW to Low Z <sup>[7]</sup>	3	-	ns	
t <sub>HZCE</sub>	CE HIGH to High Z <sup>[7, 8]</sup>	_	4	ns	
t <sub>PU</sub>	CE LOW to Power Up	0	_	ns	
t <sub>PD</sub>	CE HIGH to Power Down	_	8	ns	
t <sub>DBE</sub>	Byte Enable to Data Valid	_	5	ns	
t <sub>LZBE</sub>	Byte Enable to Low Z	0	-	ns	
t <sub>HZBE</sub>	Byte Disable to High Z	_	5	ns	
Write Cycle [9,	10]	·			
t <sub>WC</sub>	Write Cycle Time	8	_	ns	
t <sub>SCE</sub>	CE LOW to Write End	6	-	ns	
t <sub>AW</sub>	Address Setup to Write End	6	_	ns	
t <sub>HA</sub>	Address Hold from Write End	0	-	ns	
t <sub>SA</sub>	Address Setup to Write Start	0	_	ns	
t <sub>PWE</sub>	WE Pulse Width	6	-	ns	
t <sub>SD</sub>	Data Setup to Write End	4	_	ns	
t <sub>HD</sub>	Data Hold from Write End	0	_	ns	
t <sub>LZWE</sub>	WE HIGH to Low Z <sup>[7]</sup>	3	_	ns	
t <sub>HZWE</sub>	WE LOW to High Z <sup>[7, 8]</sup>	-	4	ns	
t <sub>BW</sub>	Byte Enable to End of Write	6	_	ns	

#### Notes

- 5. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, and input pulse levels of 0 to 3.0 V.

  6. t<sub>POWER</sub> gives the minimum amount of time that the power supply is at typical V<sub>CC</sub> values until the first memory access is performed.

  7. At any temperature and voltage condition, t<sub>HZCE</sub> is less than t<sub>LZCE</sub>, t<sub>HZBE</sub> is less than t<sub>LZDE</sub>, t<sub>HZCE</sub> and t<sub>HZWE</sub> is less than t<sub>LZWE</sub> for any device.

  8. t<sub>HZOE</sub>, t<sub>HZCE</sub>, t<sub>HZBE</sub>, and t<sub>HZWE</sub> are specified with a load capacitance of 5 pF as in part (d) of Figure 2 on page 6. Transition is measured ±500 mV from steady state voltage.
- 9. The internal write time of the memory is defined by the overlap of CE LOW, WE LOW, and BHE/BLE LOW. CE, WE, and BHE/BLE must be LOW to initiate a write. The transition of these signals terminate the write. The input data setup and hold timing is referenced to the leading edge of the signal that terminates the write.

  10. The minimum Write cycle time for Write Cycle No. 3 (WE Controlled, OE LOW) is the sum of tsD and thzwe.



# **Switching Waveforms**

Figure 3. Read Cycle No. 1 (Address Transition Controlled) [11, 12]

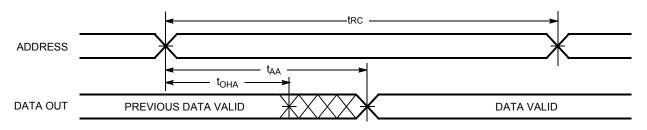
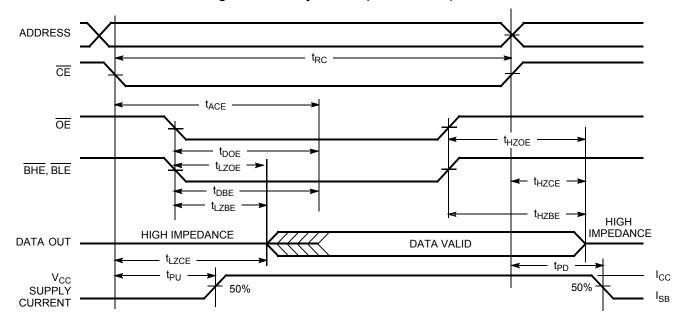


Figure 4. Read Cycle No. 2 (OE Controlled) [12, 13]



<sup>11. &</sup>lt;u>Dev</u>ice is continuously selected. <u>OE</u>, <u>CE</u>, <u>BHE</u>, and/or <u>BLE</u> = V<sub>IL</sub>. 12. WE is HIGH for read cycle.

<sup>13.</sup> Address valid prior to or coincident with  $\overline{\text{CE}}$  transition LOW.



# Switching Waveforms (continued)

Figure 5. Write Cycle No. 1 (CE Controlled) [14, 15]

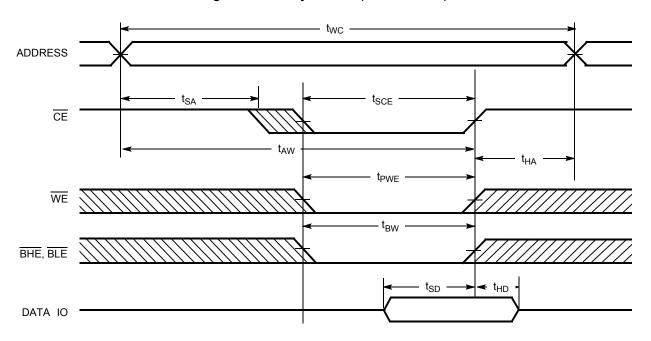
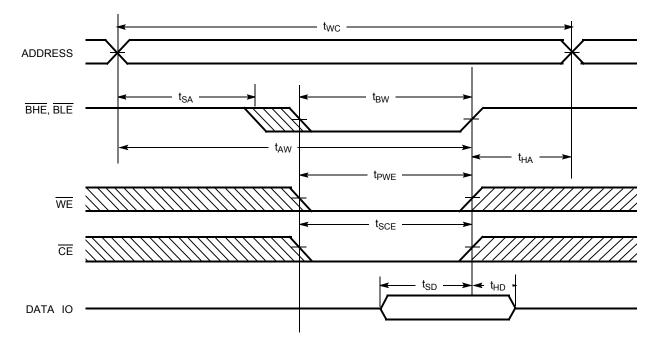


Figure 6. Write Cycle No. 2 (BLE or BHE Controlled)



#### Notes

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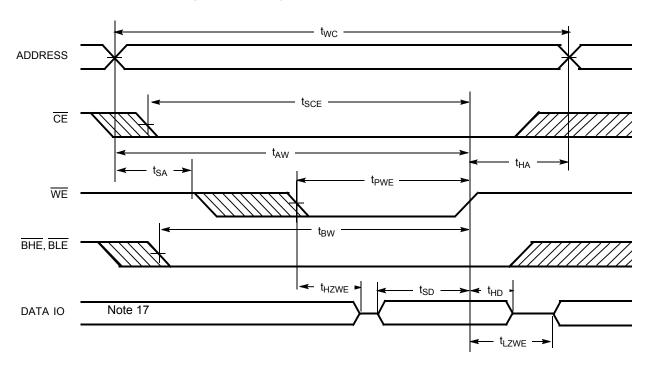
<sup>14.</sup> Data IO is high impedance if  $\overline{OE}$ ,  $\overline{BHE}$ , and/or  $\overline{BLE} = V_{IH}$ .

<sup>15.</sup> If  $\overline{\text{CE}}$  goes HIGH simultaneously with  $\overline{\text{WE}}$  going HIGH, the output remains in a high impedance state.



# Switching Waveforms (continued)

Figure 7. Write Cycle No. 3 (WE Controlled, OE LOW) [16]



<sup>16.</sup> The minimum write cycle pulse width should be equal to the sum of  $t_{\rm SD}$  and  $t_{\rm HZWE}$ . 17. During this time I/Os are in output state. Do not apply input signal.



# **Truth Table**

CE	OE	WE	BLE	BHE	I/O <sub>0</sub> –I/O <sub>7</sub>	I/O <sub>8</sub> -I/O <sub>15</sub>	Mode	Power
Н	Χ	Χ	Χ	Χ	High Z	High Z	Power Down	Standby (I <sub>SB</sub> )
L	L	Н	L	L	Data Out	Data Out	Read – All Bits	Active (I <sub>CC</sub> )
			L	Н	Data Out	High Z	Read – Lower Bits Only	Active (I <sub>CC</sub> )
			Н	L	High Z	Data Out	Read – Upper Bits Only	Active (I <sub>CC</sub> )
L	Χ	L	L	L	Data In	Data In	Write – All Bits	Active (I <sub>CC</sub> )
			L	Н	Data In	High Z	Write – Lower Bits Only	Active (I <sub>CC</sub> )
			Н	L	High Z	Data In	Write – Upper Bits Only	Active (I <sub>CC</sub> )
L	Н	Н	Х	Х	High Z	High Z	Selected, Outputs Disabled	Active (I <sub>CC</sub> )
L	Х	Х	Н	Н	High Z	High Z	Selected, Outputs Disabled	Active (I <sub>CC</sub> )



# **Ordering Information**

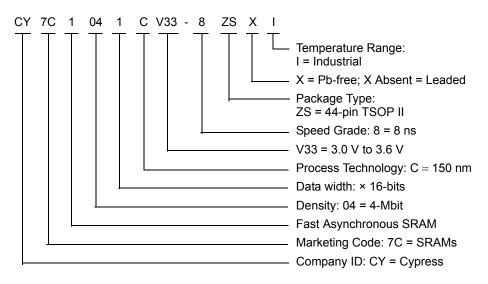
Cypress offers other versions of this type of product in many different configurations and features. The below table contains only the list of parts that are currently available. For a complete listing of all options, visit the Cypress website at <a href="https://www.cypress.com/products">www.cypress.com/products</a> or contact your local sales representative.

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Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
8	CY7C1041CV33-8ZSXI	51-85087	44-pin TSOP Type II (Pb-free)	Industrial

Please contact your local Cypress sales representative for availability of these parts

#### **Ordering Code Definitions**

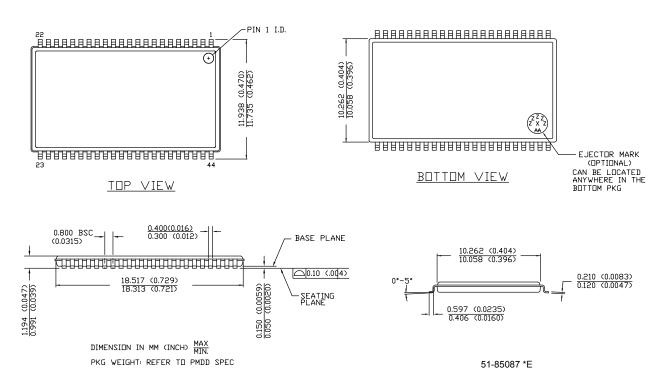


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# **Package Diagram**

Figure 8. 44-pin TSOP Z44-II Package Outline, 51-85087





# **Acronyms**

Acronym	Description			
CE	Chip Enable			
CMOS	Complementary Metal Oxide Semiconductor			
I/O	Input/Output			
OE	Output Enable			
SRAM	Static Random Access Memory			
TSOP	Thin Small Outline Package			
TTL	Transistor-Transistor Logic			
WE	Write Enable			

# **Document Conventions**

# **Units of Measure**

Symbol	Unit of Measure			
°C	degree Celsius			
MHz	megahertz			
μΑ	microampere			
μs	microsecond			
mA	milliampere			
mm	millimeter			
ms	millisecond			
mW	milliwatt			
ns	nanosecond			
Ω	ohm			
%	percent			
pF	picofarad			
V	volt			
W	watt			



# **Document History Page**

Rev.	ECN No.	Issue Date	Orig. of Change	Description of Change
**	109513	12/13/01	HGK	New data sheet
*A	112440	12/20/01	BSS	Updated 51-85106 from revision *A to *C
*B	112859	03/25/02	DFP	Added CY7C1042CV33 in BGA package Removed 1042 BGA option pin ACC Final Data Sheet
*C	116477	09/16/02	CEA	Add applications foot note to data sheet
*D	119797	10/21/02	DFP	Added 20-ns speed bin
*E	262949	See ECN	RKF	Added Lead (Pb)-Free parts in the Ordering info (Page #9)     Added Automotive Specs to Datasheet
*F	361795	See ECN	SYT	Added Pb-Free offerings in the Ordering Information
*G	435387	See ECN	NXR	Removed -8 Speed bin from Product offering. Corrected typo in description for BHE/BLE in pin definitions table on Page# corrected their Pin name from OE2 to OE. Included the Maximum Ratings for Static Discharge Voltage and Latch u Current. Changed the description of I <sub>IX</sub> current from Input Load Current to Input Leakage Current Added note# 4 on page# 4 Updated the Ordering Information table
*H	499153	See ECN	NXR	Added Automotive-A Operating Range Changed t <sub>power</sub> value from 1 μs to 100 μs Updated Ordering Information table
*	2104110	See ECN	VKN/AESA	Added Automotive-E specs for 12 ns speed Updated Ordering Information table
*J	2897141	03/22/10	AJU/VIVG	Updated Ordering Information (Removed inactive parts). Updated Package Diagram.
*K	3072834	11/12/2010	PRAS	Updated Ordering Information: Removed inactive parts. Added Ordering Code Definitions.
*L	3186840	03/03/2011	PRAS	Updated Features. Updated Selection Guide (Added -8 ns speed grade devices and removed -1 ns, -12 ns, -15 ns and -20 ns speed grade devices). Removed Figure "48-Ball FBGA Pinout (Top View)" and renamed Figure "44-Pin SOJ/TSOP II (Top View)" as "44-pin TSOP II (Top View)" in Pin Configurations. Updated Pin Definitions (Deleted the column "BGA Pin Number" and renamed the column "SOJ, TSOP Pin Number" as "TSOP Pin Number". Updated Operating Range Updated Electrical Characteristics (Added -8 ns speed grade devices ar removed -10 ns, -12 ns, -15 ns and -20 ns speed grade devices). Updated Thermal Resistance (Deleted the columns SOJ and FBGA). Updated Switching Characteristics (Added -8 ns speed grade devices ar removed -10 ns, -12 ns, -15 ns and -20 ns speed grade devices). Updated Ordering Information (Added new speed bin (-8 ns speed grade devices) and removed -10 ns, -12 ns, -15 ns and -20 ns speed grade devices Added Acronyms and Units of Measure. Dislodged Automotive information to new datasheet (001-67307) Removed SOJ and FBGA package related information in all instances in the document. Updated to new template.



# **Document History Page** (continued)

	Document Title: CY7C1041CV33, 4-Mbit (256 K × 16) Static RAM Document Number: 38-05134						
Rev.	ECN No.	Issue Date	Orig. of Change	Description of Change			
*M	3199948	03/18/2011	PRAS	Updated Features (Updated Operating Temperature Range from Commercial to Industrial). Updated Operating Range (Updated Operating Temperature Range from Commercial to Industrial). Updated Ordering Information (Updated Operating Temperature Range from Commercial to Industrial).			
*N	3266084	05/28/2011	PRAS	Updated Functional Description (Removed "For best practice recommendations, refer to the Cypress application note AN1064, SRAM System Guidelines.").			
*0	4315741	03/20/2014	VINI	Updated Package Diagram: spec 51-85087 – Changed revision from *C to *E. Updated to new template. Completing Sunset Review.			
*P	4578447	01/16/2015	VINI	Added related documentation hyperlink in page 1. Updated Switching Waveforms: Added Note 16 and referred the same note in Figure 7.			
*Q	4702949	03/27/2015	VINI	Updated Switching Waveforms: Added Note 17 and referred the same note in DATA IO in Figure 7. Completing Sunset Review.			
*R	5962455	11/09/2017	AESATMP8	Updated logo and Copyright.			



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